

TENTATIVE TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W34FU, TC7W34FK

(UNDER DEVELOPMENT)

TRIPLE NON-INVERT BUFFER

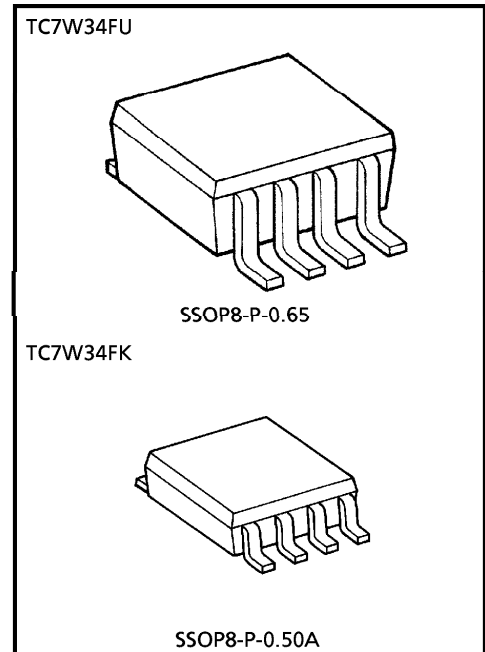
The TC7W34FU is high speed CMOS BUFFER fabricated with silicon gate CMOS technology.

The internal circuit is composed of 2 stage including buffer output, which enable high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

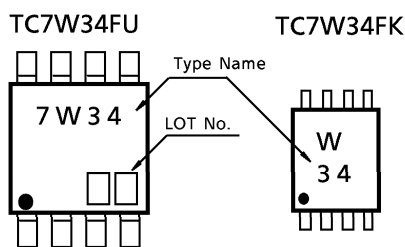
FEATURES

- High Speed $t_{pd} = 6ns$ (Typ.) at $V_{CC} = 5V$
- Low Power Dissipation $I_{CC} = 1\mu A$ (Max.) at $T_a = 25^\circ C$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = |I_{OL}| = 4mA$ (Min.)
- Balanced Propagation Delays..... $t_{pLH} = t_{pHL}$
- Wide Operating Voltage Range... $V_{CC} (opr) = 2\sim 6V$



Weight
 SSOP8-P-0.65 : 0.02g (Typ.)
 SSOP8-P-0.50A : 0.01g (Typ.)

MARKING



TRUTH TABLE

A	Y
L	L
H	H

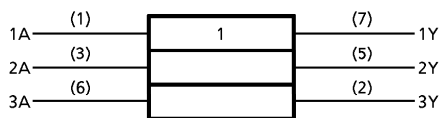
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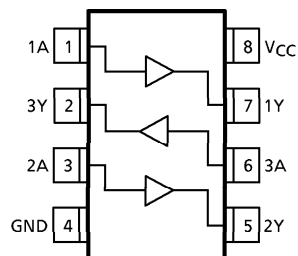
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	- 0.5~7	V
DC Input Voltage	V _{IN}	- 0.5~V _{CC} + 0.5	V
DC Output Voltage	V _{OUT}	- 0.5~V _{CC} + 0.5	V
Input Diode Current	I _{IK}	± 20	mA
Output Diode Current	I _{OK}	± 20	mA
DC Output Current	I _{OUT}	± 25	mA
DC V _{CC} / Ground Current	I _{CC}	± 25	mA
Power Dissipation	P _D	300	mW
Storage Temperature	T _{stg}	- 65~150	°C
Lead Temperature (10 s)	T _L	260	°C

LOGIC DIAGRAM



PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	2~6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C
Input Rise and Fall Time	t _r , t _f	0~1000 (V _{CC} = 2.0V)	ns
		0~500 (V _{CC} = 4.5V)	
		0~400 (V _{CC} = 6.0V)	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC}	Ta = 25°C			Ta = -40~85°C		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High-Level Input Voltage	V _{IH}		2.0	1.5	—	—	1.5	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.2	—	—	4.2	—		
Low-Level Input Voltage	V _{IL}		2.0	—	—	0.5	—	0.5	V	
			4.5	—	—	1.35	—	1.35		
			6.0	—	—	1.8	—	1.8		
High-Level Output Voltage	V _{OH}	V _{IN} = V _{IH}	I _{OH} = -20μA	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
			I _{OH} = -4mA	4.5	4.18	4.31	—	4.13	—	
				6.0	5.68	5.80	—	5.63	—	
Low-Level Output Voltage	V _{OL}	V _{IN} = V _{IL}	I _{OL} = 20μA	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
				6.0	—	0.0	0.1	—	0.1	
			I _{OL} = 4mA	4.5	—	0.17	0.26	—	0.33	
6.0	—	0.18		0.26	—	0.33				
Input Leakage Current	I _{IN}	V _{IN} = V _{CC} or GND	6.0	—	—	±0.1	—	±1.0	μA	
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	6.0	—	—	1.0	—	10.0	μA	

AC ELECTRICAL CHARACTERISTICS (C_L = 15pF, V_{CC} = 5V, Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			UNIT
			MIN.	TYP.	MAX.	
Output Transition Time	t _{TLH} t _{THL}	—	—	4	8	ns
Propagation Delay Time	t _{pLH} t _{pHL}	—	—	6	12	ns

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input t_r = t_f = 6ns)

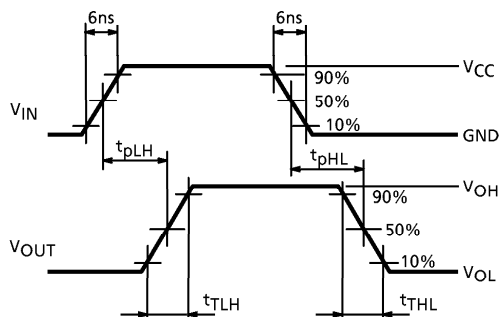
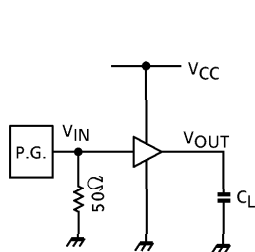
CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC}	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t _{TLH} t _{THL}	—	2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time	t _{pLH} t _{pHL}	—	2.0	—	27	75	—	95	ns
			4.5	—	9	15	—	19	
			6.0	—	8	13	—	16	
Input Capacitance	C _{IN}	—	—	5	10	—	10	pF	
Power Dissipation Capacitance	C _{PD}	(Note 1)	—	20	—	—	—	pF	

(Note 1) : C_{PD} is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation hereunder.

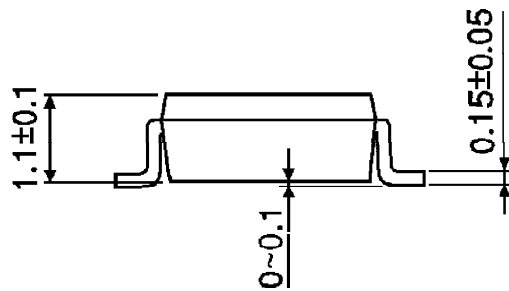
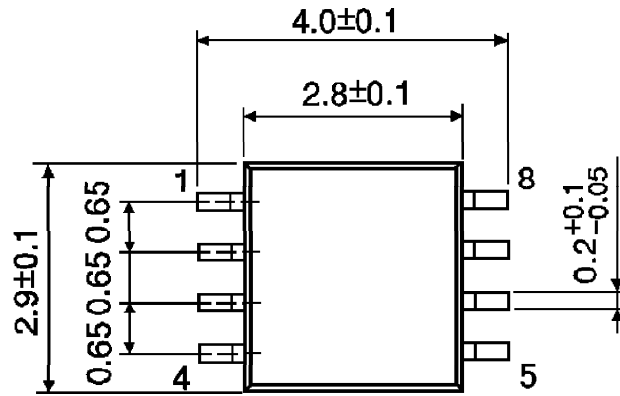
$$I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 3 \text{ (per gate)}$$

SWITCHING CHARACTERISTICS TEST CIRCUIT



OUTLINE DRAWING
SSOP8-P-0.65

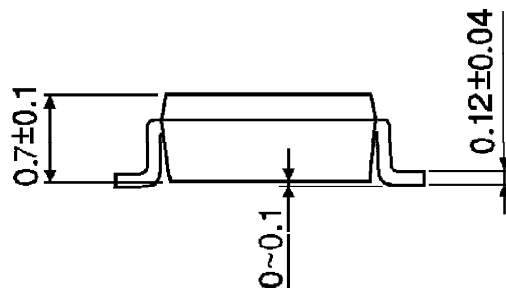
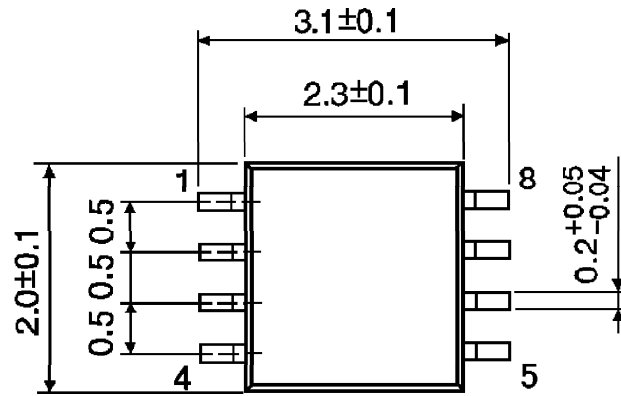
Unit : mm



Weight : 0.02g (Typ.)

OUTLINE DRAWING
SSOP8-P-0.50A

Unit : mm



Weight : 0.01g (Typ.)